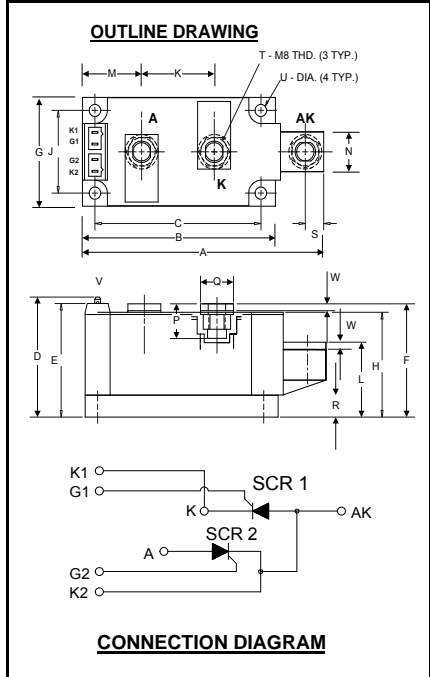


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POW-R-BLOK™ Dual SCR Isolated Module 250 Amperes / 2000 Volts



ND432025
Dual SCR Isolated
POW-R-BLOK™ Module
250 Amperes / 2000 Volts

Description:

Powerex Dual SCR Modules are designed for use in applications requiring phase control and isolated packaging. The modules are isolated for easy mounting with other components on a common heatsink. POW-R-BLOK™ has been tested and recognized by the Underwriters Laboratories.

Features:

- Electrically Isolated Heatsinking
- Aluminum Nitride Insulator
- Compression Bonded Elements
- Metal Baseplate
- Low Thermal Impedance for Improved Current Capability
- Quick Connect Gate Terminal with Provision for Keyed Mating Plug
- UL Recognized

ND43 Outline Dimensions

Dimension	Inches	Millimeters
A	4.57	116
B	3.66	93
C	3.15	80.0
D	2.17	55.1
E	2.06	52.3
F	2.07	52.0
G	1.97	50.0
H	1.90	48.3
J	1.50	38.1
K	1.38	35.0
L	1.26	32.0
M	1.122	28.5
N	.71	18.0
P	.57	14.5
Q	.625	15.9
R	.394	10.00
S	.350	8.9
T	M8 Metric	M8
U	.250 Dia.	6.35 Dia.
V	.110 x .032	2.8 x 0.8
W	.12	3.0

Note: Dimensions are for reference only.

Ordering Information:

Select the complete eight digit module part number from the table below.

Example: ND432025 is a 2000Volt, 250 Ampere Dual SCR Isolated POW-R-BLOK™ Module

Type	Voltage Volts (x100)	Current Amperes (x 10)
ND43	20	25

Benefits:

- No Additional Insulation Components Required
- Easy Installation
- No Clamping Components Required
- Reduce Engineering Time

Applications:

- Bridge Circuits
- AC & DC Motor Drives
- Battery Supplies
- Power Supplies
- Large IGBT Circuit Front Ends

Absolute Maximum Ratings

Characteristics	Conditions	Symbol		Units
Repetitive Peak Forward and Reverse Blocking Voltage		V_{DRM} & V_{RRM}	up to 2000	V
Non-Repetitive Peak Reverse Blocking Voltage ($t < 5$ msec)		V_{RSM}	2100	V
RMS Forward Current	180° Conduction, $T_C=83^\circ\text{C}$	$I_{T(RMS)}$	393	A
Average Forward Current	180° Conduction, $T_C=83^\circ\text{C}$	$I_{T(AV)}$	250	A
Peak One Cycle Surge Current, Non-Repetitive	60 Hz, 100% V_{RRM} reapplied, $T_j=130\text{C}$	I_{TSM}	8800	A
	60 Hz, No V_{RRM} reapplied, $T_j=130\text{C}$	I_{TSM}	10,420	A
	60 Hz, 100% V_{RRM} reapplied, $T_j=25\text{C}$	I_{TSM}	10,120	A
	60 Hz, No V_{RRM} reapplied, $T_j=25\text{C}$	I_{TSM}	11,900	A
Peak Three Cycle Surge Current, Non-Repetitive	60 Hz, 100% V_{RRM} reapplied, $T_j=130\text{C}$	I_{TSM}	4400	A
Peak Ten Cycle Surge Current, Non-Repetitive	60 Hz, 100% V_{RRM} reapplied, $T_j=130\text{C}$	I_{TSM}	3925	A
I^2t for Fusing for One Cycle, 8.3 milliseconds	60 Hz, 100% V_{RRM} reapplied, $T_j=130\text{C}$	I^2t	320,000	$\text{A}^2 \text{sec}$
	60 Hz, 100% V_{RRM} reapplied, $T_j=25\text{C}$	I^2t	426,720	$\text{A}^2 \text{sec}$
Maximum Rate-of-Rise of On-State Current, (Non-Repetitive)	$T_j=25^\circ\text{C}$, $I_G=500\text{mA}$, $V_D=0.67 V_{DRM}(\text{Rated})$, $I_{TM} = \pi I_{T(AV)}$, $T_r < 0.5\mu\text{s}$, $t_p > 6\mu\text{s}$	di/dt	800	$\text{A}/\mu\text{s}$
Peak Gate Power Dissipation		P_{GM}	16	W
Average Gate Power Dissipation		$P_{G(AV)}$	3	W
Peak Forward Gate Current		I_{GFM}	4	A
Peak Forward Gate Voltage		V_{GFM}	10	V
Peak Reverse Gate Voltage		V_{GRM}	5	V
Operating Temperature		T_J	-40 to +130	$^\circ\text{C}$
Storage Temperature		T_{stg}	-40 to +150	$^\circ\text{C}$
Max. Mounting Torque, M6 Mounting Screw			45	in.-Lb.
			5	Nm
Max. Mounting Torque, M8 Terminal Screw			110	in.-Lb.
			12	Nm
Module Weight, Typical			840	G
			1.85	lb
V Isolation @ 25C		V_{TIS}	2500	V

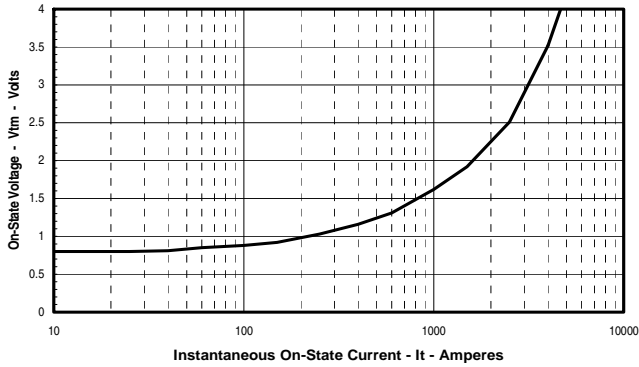
Electrical Characteristics, $T_J=25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Max.	Units
Repetitive Peak Forward Leakage Current	I_{DRM}	Up to 2000V, $T_J=130^\circ\text{C}$		50	mA
Repetitive Peak Reverse Leakage Current	I_{RRM}	Up to 2000V, $T_J=130^\circ\text{C}$		50	mA
Peak On-State Voltage	V_{FM}	$I_{TM}=625\text{A}$		1.40	V
Threshold Voltage, Low-level	$V_{(TO)1}$	$T_J = 130^\circ\text{C}$, $I = 15\%I_{T(AV)}$ to $I_{T(AV)}$		0.813	V
Slope Resistance, Low-level	r_{T1}			0.810	$\text{m}\Omega$
Threshold Voltage, High-level	$V_{(TO)2}$	$T_J = 130^\circ\text{C}$, $I = I_{T(AV)}$ to I_{TSM}		0.947	V
Slope Resistance, High-level	r_{T2}			0.641	$\text{m}\Omega$
V_{TM} Coefficients, Full Range		$T_J = 130^\circ\text{C}$, $I = 15\%I_{T(AV)}$ to I_{TSM}	A =	0.7324	
			B =	9.80 E-3	
		$V_{TM} = A + B \ln I + C I + D \text{Sqrt } I$	C =	5.83 E-4	
			D =	6.02 E-3	
Minimum dV/dt	dV/dt	Exponential to $2/3 V_{DRM}$ $T_J=130^\circ\text{C}$, Gate Open	500		$\text{V}/\mu\text{s}$
Turn-On Time (Typical)	t_{on}	$I_{TM} = 100\text{A}$, $V_D = 100\text{V}$	7	(Typical)	μs
Turn-Off Time (Typical)	t_{off}	$T_J = 130^\circ\text{C}$, $I_T = 250\text{A}$ Re-Applied $dV/dt = 20\text{V}/\mu\text{s}$ Linear to $0.8 V_{DRM}$	150	(Typical)	μs
Gate Trigger Current	I_{GT}	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$		150	mA
Gate Trigger Voltage	V_{GT}	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$		3.0	Volts
Non-Triggering Gate Voltage	V_{GDM}	$T_J=130^\circ\text{C}$, $V_D = 1/2 V_{DRM}$		0.15	Volts

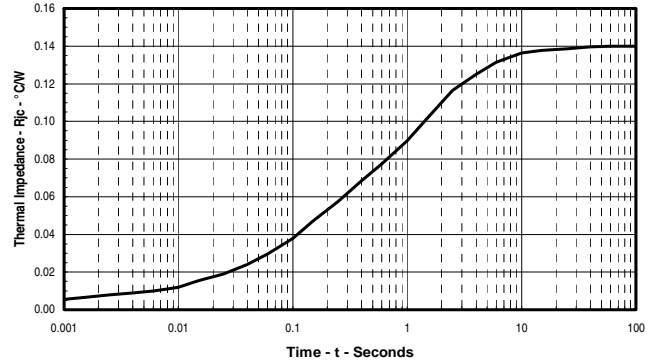
Thermal Characteristics

Characteristics	Symbol		Max.	Units
Thermal Resistance, Junction to Case	$R_{\theta J-C}$	Per Module, both conducting Per Junction both conducting	0.07 0.14	$^\circ\text{C}/\text{W}$ $^\circ\text{C}/\text{W}$
Thermal Impedance Coefficients	$Z_{\theta J-C}$	$Z_{\theta J-C} = K_1 (1 - \exp(-t/\tau_1))$ $+ K_2 (1 - \exp(-t/\tau_2))$ $+ K_3 (1 - \exp(-t/\tau_3))$ $+ K_4 (1 - \exp(-t/\tau_4))$	$K_1 = 5.27\text{E-}3$ $K_2 = 1.17\text{E-}2$ $K_3 = 5.26\text{E-}2$ $K_4 = 6.97\text{E-}2$	$\tau_1 = 1.69\text{E-}4$ $\tau_2 = 2.07\text{E-}2$ $\tau_3 = 2.37\text{E-}1$ $\tau_4 = 2.46$
Thermal Resistance, Case to Sink Lubricated	$R_{\theta C-S}$	Per Module	0.03	$^\circ\text{C}/\text{W}$

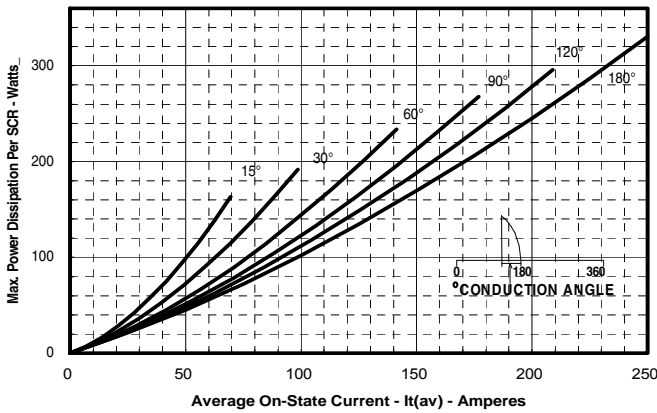
Maximum On-State Forward Voltage Drop
($T_j = 130^\circ\text{C}$)



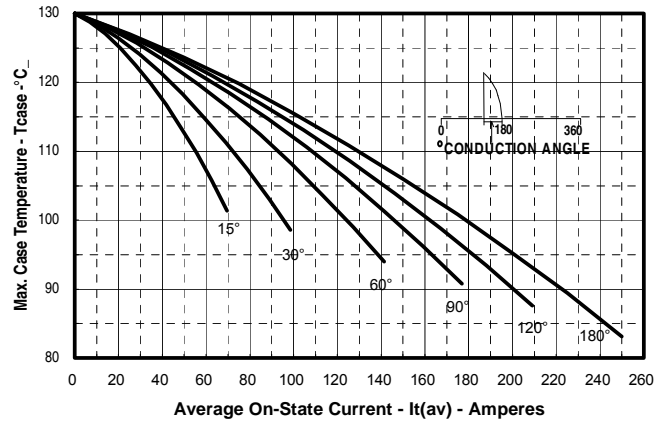
Maximum Transient Thermal Impedance
(Junction To Case)



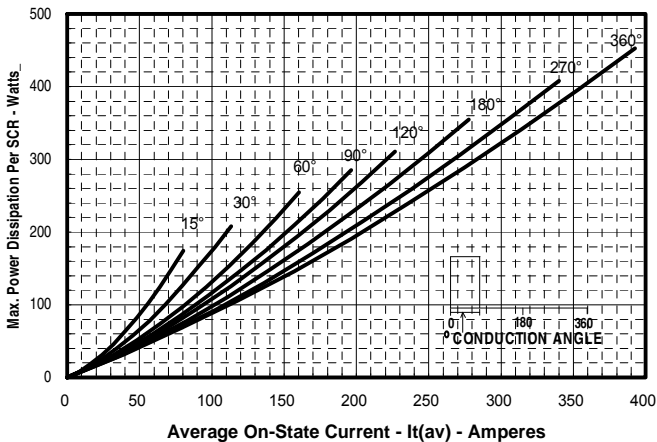
Maximum On-State Power Dissipation
(Sinusoidal Waveform)



Maximum Allowable Case Temperature
(Sinusoidal Waveform)



Maximum On-State Power Dissipation
(Rectangular Waveform)



Maximum Allowable Case Temperature
(Rectangular Waveform)

